Amendments to the Specification:

Please replace paragraph [0005] beginning at line 1 on page 2, with the following amended paragraph:

[0005] This application incorporates by reference herein in its entirety, the commonly-owned and concurrently filed U.S. Application No. [UNKNOWN], Attorney Docket BOX016 US, Client Docket AMAT 008546USA 10/813,407 entitled "High Throughput Measurement Of Via Defects In Interconnects" filed by Jiping Li et al.

Please replace the paragraph [0044] at page 14, with the following amended paragraph:

[0044] Therefore, the duration Δt (between times t1 and t6 in FIG. 1E) times t2 and t6 in FIG. 1D) is selected to be sufficiently small to ensure that a temperature rise due to presence of heat from beam 111 is noticeable in the hot image. In some embodiments, duration Δt is selected to be the time at which the temperature after time t2 falls to (1/e) of the steady state value during period t1-t2. In other embodiments, duration Δt is selected experimentally, after trial and error with different durations, to find subsurface defects as described next. In some embodiments, duration Δt is on the order of a few microseconds (e.g. 2-3 microseconds).

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